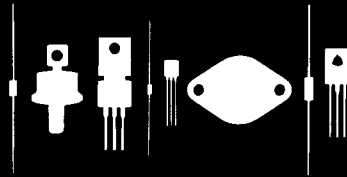


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145 Adams Avenue  
Hauppauge, New York 11788



2N6473 2N6474 NPN  
2N6475 2N6476 PNP

COMPLEMENTARY SILICON  
SWITCHING TRANSISTORS

JEDEC TO-220 CASE

### DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N6473 Series types are complementary silicon power transistors manufactured by the epitaxial base process designed for general purpose amplifier and switching applications.

### MAXIMUM RATINGS ( $T_C=25^\circ\text{C}$ unless otherwise noted)

	SYMBOL	2N6473	2N6474	UNIT
		2N6475	2N6476	
Collector-Base Voltage	V <sub>CB0</sub>	110	130	V
Collector-Emitter Voltage ( $R_{BE}=100\Omega$ )	V <sub>CER</sub>	110	130	V
Collector-Emitter Voltage	V <sub>CEO</sub>	100	120	V
Emitter-Base Voltage	V <sub>EBO</sub>		5.0	V
Collector Current	I <sub>C</sub>		4.0	A
Base Current	I <sub>B</sub>		2.0	A
Power Dissipation	P <sub>D</sub>		40	W
Operating and Storage Junction Temperature	T <sub>J</sub> , T <sub>stg</sub>	-65 TO +150		°C
Thermal Resistance	$\theta_{JC}$	3.125		°C/W

### ELECTRICAL CHARACTERISTICS ( $T_C=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	2N6473		2N6474		UNIT	
		2N6475	MIN	MAX	MIN		MAX
I <sub>CEV</sub>	V <sub>CE</sub> =Rated V <sub>CEO</sub> , V <sub>BE</sub> =1.5V			0.1		0.1	mA
I <sub>CEV</sub>	V <sub>CE</sub> =Rated V <sub>CEO</sub> , V <sub>BE</sub> =1.5V, T <sub>C</sub> =100°C			2.0		2.0	mA
I <sub>CER</sub>	V <sub>CE</sub> =Rated V <sub>CER</sub> , R <sub>BE</sub> =100Ω			0.1		0.1	mA
I <sub>CER</sub>	V <sub>CE</sub> =Rated V <sub>CER</sub> , R <sub>BE</sub> =100Ω, T <sub>C</sub> =100°C			2.0		2.0	mA
I <sub>CEO</sub>	V <sub>CE</sub> =½ Rated V <sub>CEO</sub>			1.0		1.0	mA
I <sub>EBO</sub>	V <sub>BE</sub> =5.0V			1.0		1.0	mA
BV <sub>CEO</sub>	I <sub>C</sub> =100mA	100			120		V
BV <sub>CER</sub>	I <sub>C</sub> =100mA, R <sub>BE</sub> =100Ω	110			130		V
V <sub>CE</sub> (SAT)	I <sub>C</sub> =1.5A, I <sub>B</sub> =0.15A			1.2		1.2	V
V <sub>CE</sub> (SAT)	I <sub>C</sub> =4.0A, I <sub>B</sub> =2.0A			2.5		2.5	V
V <sub>BE</sub> (ON)	V <sub>CE</sub> =4.0V, I <sub>C</sub> =1.5A			2.0		2.0	V
V <sub>BE</sub> (ON)	V <sub>CE</sub> =2.5V, I <sub>C</sub> =4.0A			3.5		3.5	V
h <sub>FE</sub>	V <sub>CE</sub> =4.0V, I <sub>C</sub> =1.5A		15	150		15	150
h <sub>FE</sub>	V <sub>CE</sub> =2.5V, I <sub>C</sub> =4.0A		2.0			2.0	
h <sub>fe</sub>	V <sub>CE</sub> =4.0V, I <sub>C</sub> =0.5A, f=50kHz		20			20	
f <sub>T</sub>	V <sub>CE</sub> =4.0V, I <sub>C</sub> =0.5A (2N6473, 2N6474)		4.0			4.0	MHz
f <sub>T</sub>	V <sub>CE</sub> =4.0V, I <sub>C</sub> =0.5A (2N6475, 2N6476)		5.0			5.0	MHz
C <sub>ob</sub>	V <sub>CB</sub> =10V, f=1.0MHz			250		250	pF